

EPC eGaN® Half Bridge Qualification Report EPC2111



Robert Strittmatter, Director of Engineering, Efficient Power Conversion Corporation

This report summarizes the Product Qualification results for EPC part number EPC2111 which meets all required qualification requirements and is released for production.

Scope

The testing matrix in this qualification report covers the qualification of eGaN Half Bridge product EPC2111. EPC2111 has the same die process and design rules as other eGaN Half Bridge products (EPC2100–EPC2105) referenced below. EPC2111 has the same package process and bump size as EPC2045.

A qualification by similarity matrix approach is applied, with the table of part numbers formed by associated die family (same die process and design rules) and package family (same package process and design rules). The intent of qualification by similarity is that all potential failure mechanisms for the part numbers in the table are included and represented by the samples of each individual test.

All part numbers in the table with samples that have not been included in each of the individual tests listed in this report, are considered qualified by similarity in accordance with the above defined die and package families.

Part Number	Voltage (V)	R _{DS(on)} (mΩ)	Die Size (mm x mm)
EPC2104	100	6.8 / 6.8	XL (6.05 x 2.3)
EPC2032	100	4	XL (4.65 x 2.65)
EPC2001C	100	7	L (4.11 x 1.63)
EPC2103	80	5.7 / 5.7	XL (6.05 x 2.3)
EPC2105	80	15 / 3.7	XL (6.05 x 2.3)
EPC2029	80	3.2	XL (4.65 x 2.65)
EPC2101	60	11.5 / 2.7	XL (6.05 x 2.3)
EPC2102	60	4.4 / 4.4	XL (6.05 x 2.3)
EPC2100	30	8.2 / 2.0	XL (6.05 x 2.3)
EPC2045	100	7	L (2.5 x 1.5)
EPC2111	30	19 / 8.0	L (3.5 x 1.5)
EPC2106	100	70 / 70	S (1.35 x 1.35)
EPC800x	40	250	S (2.05 x 0.85)

Qualification Test Overview

EPC’s eGaN FETs were subjected to a wide variety of stress tests under conditions that are typical for silicon-based power MOSFETs. These tests included:

- High temperature reverse bias (HTRB): Parts are subjected to a drain-source voltage at the maximum rated temperature
- High temperature gate bias (HTGB): Parts are subjected to a gate source voltage at the maximum rated temperature
- High temperature storage (HTS): Parts are subjected to heat at the maximum rated temperature
- Temperature cycling (TC): Parts are subjected to alternating high- and low temperature extremes
- High temperature high humidity reverse bias (H3TRB): Parts are subjected to humidity under high temperature with a drain-source voltage applied
- Moisture sensitivity level (MSL): Parts are subjected to moisture, temperature, and three cycles of reflow.

The stability of the devices is verified with DC electrical tests after stress biasing. The electrical parameters are measured at time-zero and at interim readout points at room temperature. Electrical parameters such as the gate-source leakage, drain-source leakage, gate-source threshold voltage, and on-state resistance are compared against the data sheet specifications. A failure is recorded when a part exceeds the datasheet specifications. eGaN FETs are stressed to meet the latest Joint Electron Device Engineering Council (JEDEC) standards when possible.

For all tests in this report other than temperature cycling, parts were mounted onto FR5 (or high Tg FR4) adaptor cards. The copper layer thickness was either 1 oz. or 2 oz. For temperature cycling tests, parts were mounted on low CTE polyimide (Arlon Polyimide 85NT) adapter cards, with a Cu thickness of ½ oz. Arlon 85NT has an in-plane CTE of 7-9 ppm/°C, which is better matched to eGaN FETs (3 ppm/°C) than FR5. In all cases, adaptor cards were 1.6 mm in thickness with two copper layers. Kester Type 4 NP505-HR solder and no-clean flux was used in mounting the part onto the adaptor card.

High Temperature Reverse Bias

Parts were subjected to 80% of the rated drain-source voltage at the maximum rated temperature for a stress period of 1000 hrs. One failure was observed after 168 hours of HTRB for EPC2101. The failure analysis for this part was inconclusive. More parts will be tested to identify the failure mechanism.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (sample x lot)	Duration (Hrs)
HTRB	EPC2104	100	XL (6.05 x 2.3)	T=130°C, V _{DS} = 80 V	0	77 x 1	1000
HTRB	EPC2102	60	XL (6.05 x 2.3)	T=130°C, V _{DS} = 48 V	0	77 x 1	1000
HTRB	EPC2101	60	XL (6.05 x 2.3)	T=130°C, V _{DS} = 48 V	1	77 x 1	1000
HTRB	EPC2111	30	L (3.5 x 1.5)	T=150°C, V _{DS} = 24 V	0	77 x 1	1000

Table 1. High Temperature Reverse Bias Test

High Temperature Gate Bias

Parts were subjected to 5.5 V gate-source bias at the maximum rated temperature for a stress period of 1000 hours.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (sample x lot)	Duration (Hrs)
HTGB	EPC2103	80	XL (6.05 x 2.3)	T = 150°C, V _{GS} = 5.5 V	0	77 x 3	1000
HTGB	EPC2106	100	S (1.35 x 1.35)	T = 150°C, V _{GS} = 5.5 V	0	77 x 2	1000

Note - EPC2111 is qualified by matrix.

Table 2. High Temperature Gate Bias Test

High Temperature Storage

Parts were subjected to heat at the maximum rated temperature.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (sample x lot)	Duration (Hrs)
HTS	EPC2103	80	XL (6.05 x 2.3)	T = 150°C, Air	0	77 x 3	1000
HTS	EPC2106	100	S (1.35 x 1.35)	T = 150°C, Air	0	77 x 2	1000

Note - EPC2111 is qualified by matrix.

Table 3. High Temperature Storage Test

Temperature Cycling

Parts were subjected to temperature cycling between -40°C and +125°C for a total of 500 cycles. Dwell time of 5 minutes was used in accordance with the JEDEC Standard JESD22A104. EPC2100 – EPC2105 parts were mounted on Low CTE Polyimide (Arlon Polyimide 85NT) adapter cards. EPC2045 parts were mounted on FR5 adapter cards.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (sample x lot)	Duration (Cys)
TC	EPC2104	100	XL (6.05 x 2.3)	-40 to +125°C, Air, Low CTE Polyimide Cards	0	77 x 1	500
TC	EPC2103	80	XL (6.05 x 2.3)	-40 to +125°C, Air, Low CTE Polyimide Cards	0	77 x 2	500
TC	EPC2045	100	L (2.5 x 1.5)	-40 to +125°C, Air, FR5 Cards	0	77 x 1	1000
TC	EPC2045	100	L (2.5 x 1.5)	-40 to +125°C, Air, FR5 Cards	0	77 x 1	1000
TC	EPC2045	100	L (2.5 x 1.5)	-40 to +125°C, Air, FR5 Cards	0	77 x 1	850

Note - EPC2111 is qualified by matrix.

Table 4. Temperature Cycling Test

High Temperature High Humidity Reverse Bias

Parts were subjected to a drain-source bias at 85% RH and 85°C for a stress period of 500 hours. The testing was done in accordance with the JEDEC Standard JESD22A101.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (sample x lot)	Duration (Hrs)
H3TRB	EPC2104	100	XL (6.05 x 2.3)	T = 85°C, RH = 85%, V _{DS} = 64 V	0	35 x 1	500
H3TRB	EPC2103	80	XL (6.05 x 2.3)	T = 85°C, RH = 85%, V _{DS} = 64 V	0	36 x 1	500
H3TRB	EPC2100	30	XL (6.05 x 2.3)	T = 85°C, RH = 85%, V _{DS} = 24 V	0	36 x 1	500
H3TRB	EPC2111	30	L (3.5 x 1.5)	T = 85°C, RH = 85%, V _{DS} = 24 V	0	35 x 1	1000

Table 5. High Temperature High Humidity Reverse Bias Test

Moisture Sensitivity Level

Parts were subjected to 85% RH at 85°C for a stress period of 168 hours. The parts were also subjected to three cycles of Pb-free reflow in accordance with the IPC/JEDEC joint Standard J-STD-020.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (sample x lot)	Duration (Hrs)
MSL1	EPC2032	100	XL (4.65 x 2.65)	T = 85°C, RH = 85%, 3 reflow	0	77 x 1	168
MSL1	EPC2029	80	XL (4.65 x 2.65)	T = 85°C, RH = 85%, 3 reflow	0	25 x 2 77 x 2	168
MSL1	EPC2001C	100	L (4.11 x 1.63)	T = 85°C, RH = 85%, 3 reflow	0	25 x 1	168
MSL1	EPC800x	40	S (2.05 x 0.85)	T = 85°C, RH = 85%, 3 reflow	0	77 x 3	168

Note - EPC2111 is qualified by matrix.

Table 6. Moisture Sensitivity Level Test